

General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

Features

- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

Application

- BLDC Motor driver
- DC-DC
- Load Switch

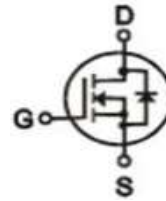
Ordering Information:

Part NO.	ZMS050N10P
Marking	ZMS050N10
Packing Information	TUBE
Basic ordering unit (pcs)	1000

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		100	V
Gate-Source Voltage ^①	V_{GS}		± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	108	A
	I_D	$T_C=75^\circ\text{C}$	88	A
	I_D	$T_C=100^\circ\text{C}$	76	A
Pulsed Drain Current ^①	I_{DM}	Pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25^\circ\text{C}$;	324	A
Total Power Dissipation	P_D	$T_C=25^\circ\text{C}$	167	W
Total Power Dissipation	P_D	$T_A=25^\circ\text{C}$	4.1	W
Operating Junction Temperature	T_J		-55 to +175	$^\circ\text{C}$
Storage Temperature	T_{STG}		-55 to +175	$^\circ\text{C}$
Single Pulse Avalanche Energy	E_{AS}	L=0.1mH, VGS=10V, Rg=25 Ω ,	140	mJ
		L=0.5mH, VGS=10V, Rg=25 Ω ,	260	mJ
ESD Level (HBM)	CLASS 2			

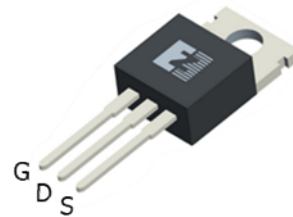
Product Summary



$$V_{DS} = 100\text{V}$$

$$R_{DS(ON)} = 5.2\text{m}\Omega$$

$$I_D = 108\text{A}$$



TO-220



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	RthJC		-	0.9	°C/W
Thermal resistance, junction-ambient	RthJA ^②		-	37	°C/W
Soldering temperature	Tsold		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250uA	100			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250uA	1.3	1.7	2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{GS} = 0V, V _{DS} = 100V			1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 25A		5.2	6.8	mΩ
	R _{DS(ON)}	V _{GS} = 4.5V, I _D = 15A		6.5	8.5	mΩ
Forward Transconductance	g _{FS}	V _{GS} = 5V, I _{SD} = 10A		28		s
Diode Forward Voltage	V _{FSD}	V _{GS} = 0V, I _{SD} = 25A			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	Ciss	f = 1MHz, V _{DS} = 25V	-	2820	-	pF
Output capacitance	Coss		-	1270	-	
Reverse transfer capacitance	Crss		-	31	-	
Gate Resistance	Rg	f = 1MHz	-	1.6		Ω
Total gate charge	Qg	V _{DD} = 15V, I _D = 20A, V _{GS} = 10V	-	34	-	nC
Gate - Source charge	Qgs		-	6.4	-	
Gate - Drain charge	Qgd		-	3.4	-	
Turn-ON Delay time	t _{D(on)}	V _{GS} = 10V, V _{DS} = 15V, R _G = 3.3Ω, I _D = 20A	-	32	-	ns
Turn-ON Rise time	t _r		-	71	-	ns
Turn-Off Delay time	t _{D(off)}		-	56	-	ns
Turn-Off Fall time	t _f		-	19	-	ns
Reverse Recovery Time	t _{RR}	V _{DD} = 20V, dI _S /dt = 100A/us, I _S = 50A	-	23	-	ns
Reverse Recovery Charge	Q _{RR}		-	120	-	nC

Fig.1 Gate-Charge Characteristics

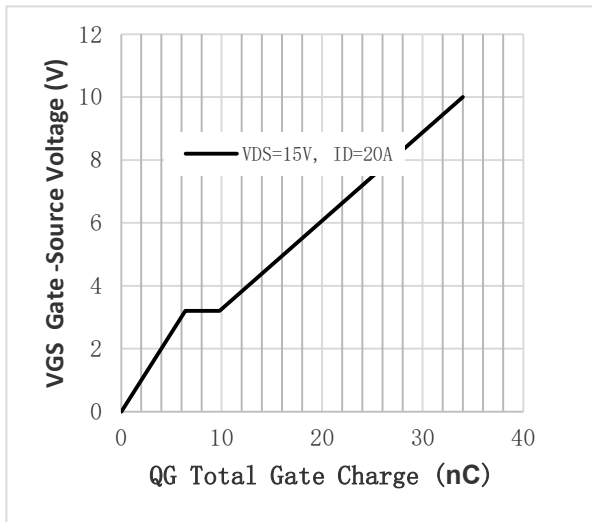


Fig.2 Capacitance Characteristics

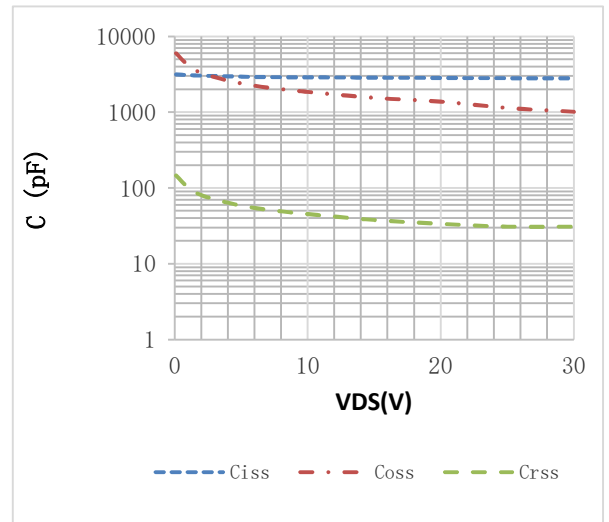


Fig.3 Power Dissipation

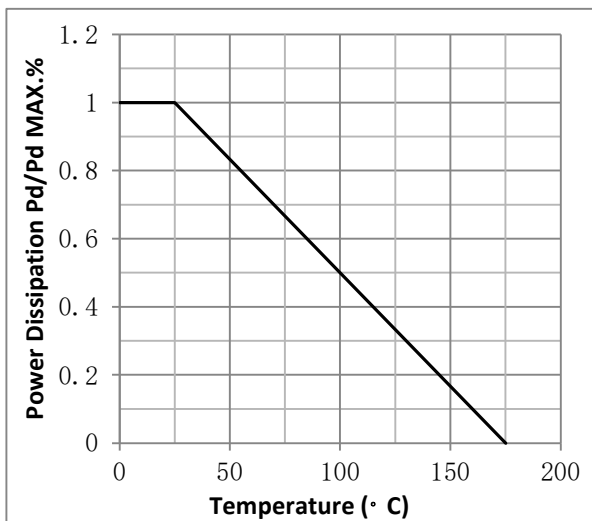


Fig.4 Typical output Characteristics

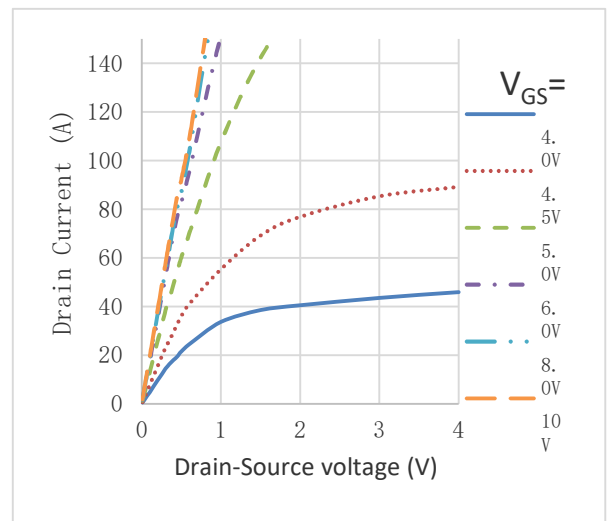


Fig.5 Threshold Voltage V.S Junction Temperature

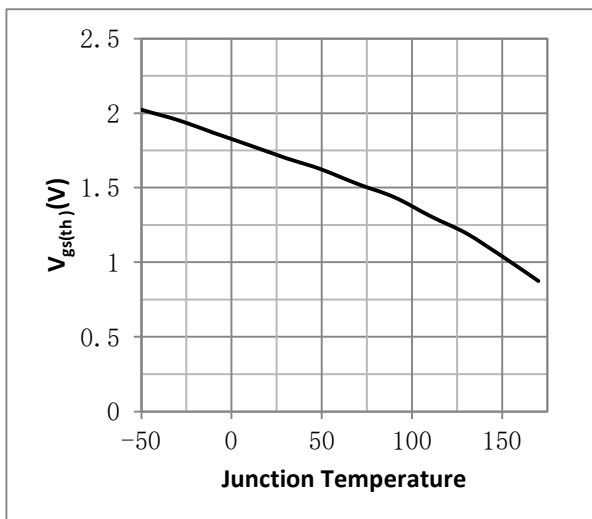


Fig.6 Resistance V.S Drain Current

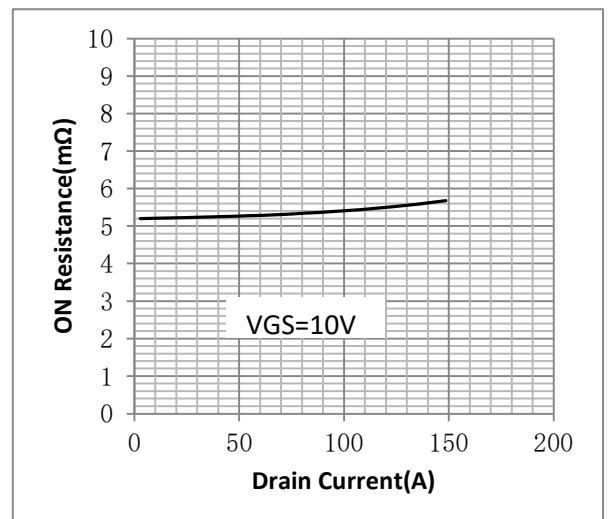


Fig.7 On-Resistance VS Gate Source Voltage

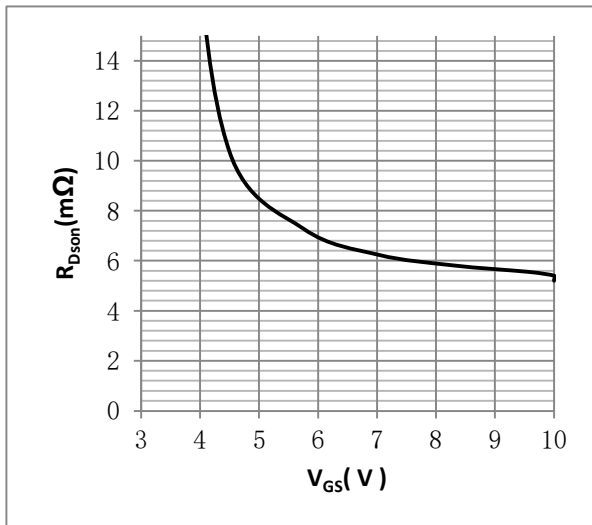


Fig.8 On-Resistance V.S Junction Temperature

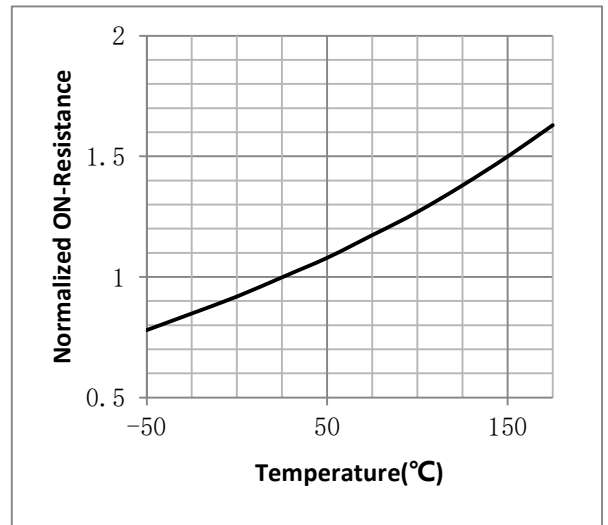


Figure 9. Diode Forward Voltage vs. Current

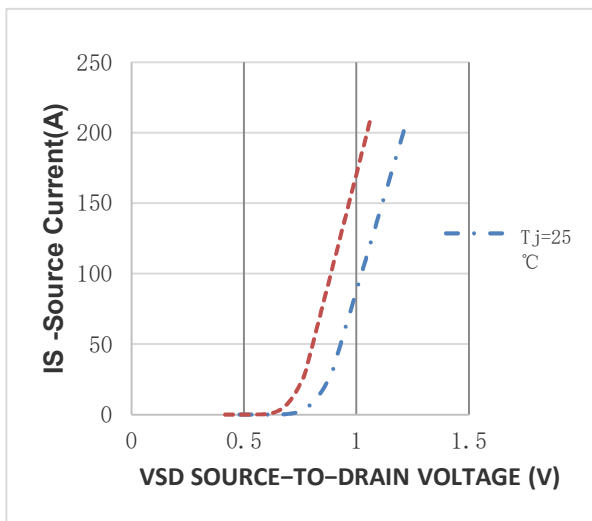


Figure 10. Transfer Characteristics

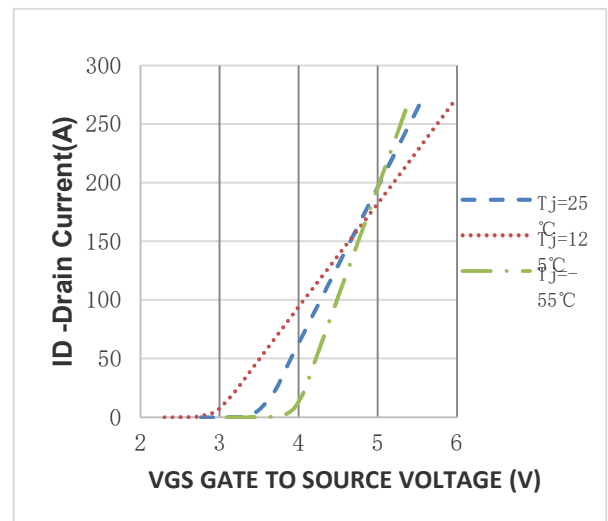


Fig.11 SOA Maximum Safe Operating Area

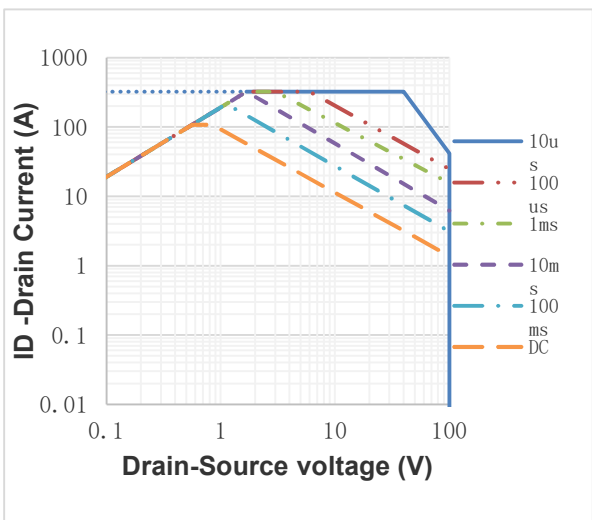
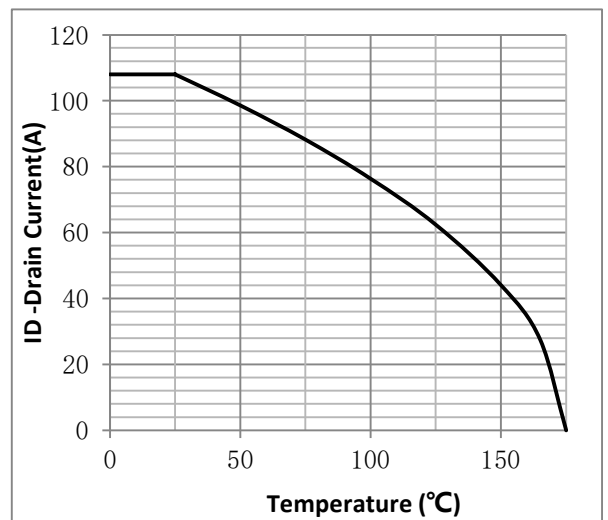
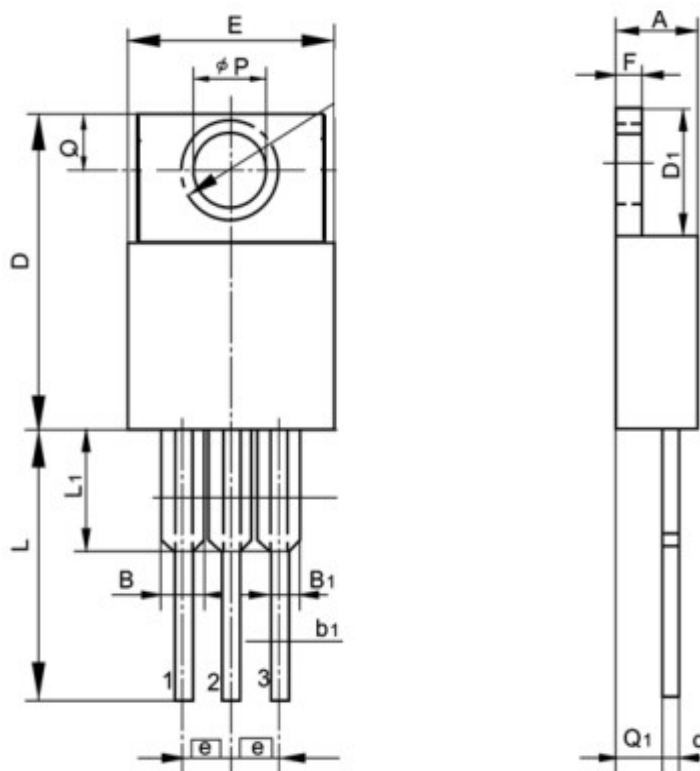


Fig.12 I_D vs. Case Temperature^③



•TO-220 Package Outline

SYMBOL	min	nom	max	SYMBOL	min	nom	max
A	4.00		4.80	E	9.90		10.70
B	1.20		1.50	e		2.54	
B1	1.00		1.40	F	1.10		1.45
b1	0.65		1.00	L	12.50		14.50
c	0.35		0.75	L1	3.00	3.50	4.00
D	15.00		16.50	Q	2.50		3.00
D1	5.90		6.90	Q1	2.00		3.00



Note:

- ① Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$, Accumulation time ≤ 50 hours; For DC , the following test conditions can be passed: $V_{GS}=+20V/-10V$, $T_j=175^{\circ}\text{C}$, $t=1000$ hours;
- ② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ③ Practically the current will be limited by PCB, thermal design and operating temperature. $V_{GS}=10V$.

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Revision History

Version	Date	Change
A	2021. 3. 16	
B	2022. 11. 22	1.Add Dynamic characteristic tf, tr etc. 2.Add Reach, HF figure, 2. ID modify